





Body Diode Reverse Recovery Time	trr	IF=20A, dI/dt=100A/μs	10	
Body Diode Reverse Recovery Charge	Qrr		16	

Note:

;

Fig.1 Power Dissipation

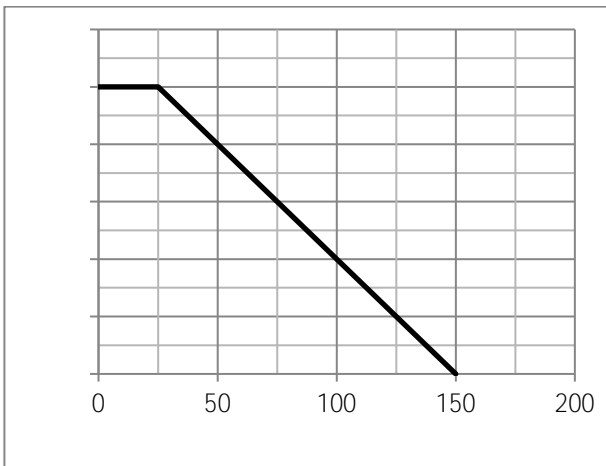


Fig.2 Typical output Characteristics

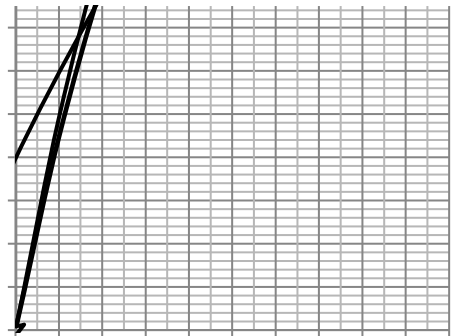


Fig.3 Threshold Voltage V.S Junction Temperature

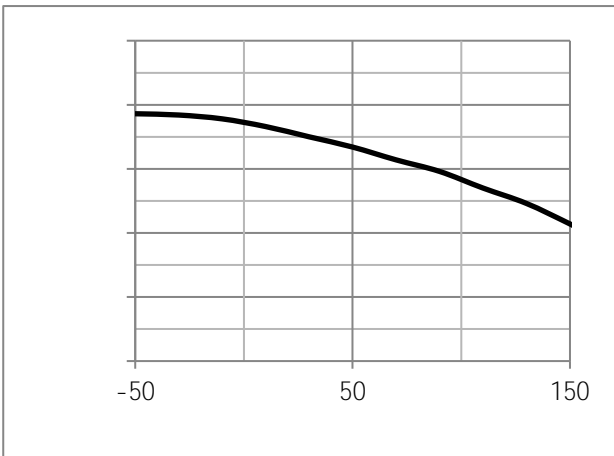


Fig.4 Resistance V.S Drain Current

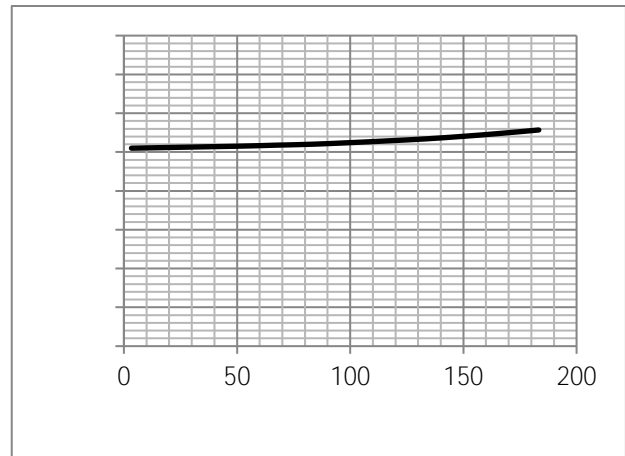


Fig.5 On-Resistance VS Gate Source Voltage

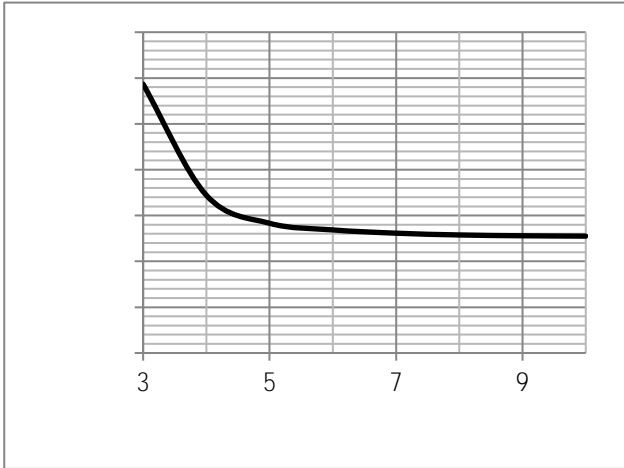


Fig.6 On-Resistance V.S Junction Temperature

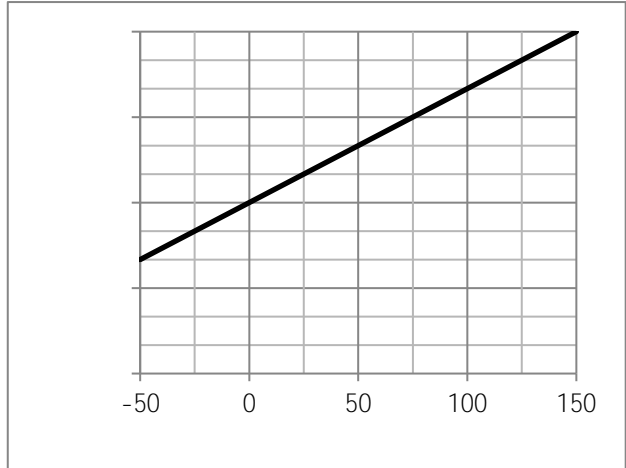


Fig.7 Gate Charge Characteristics

Fig.8 Capacitance vs Vds

Fig.9 SOA Maximum Safe Operating Area

Fig.10 ID-Junction Temperature

Fig.11 Switching Time Measurement Circuit

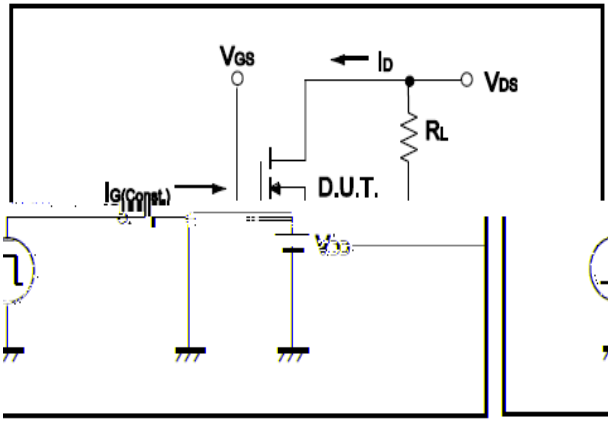


Fig.12 Gate Charge Waveform

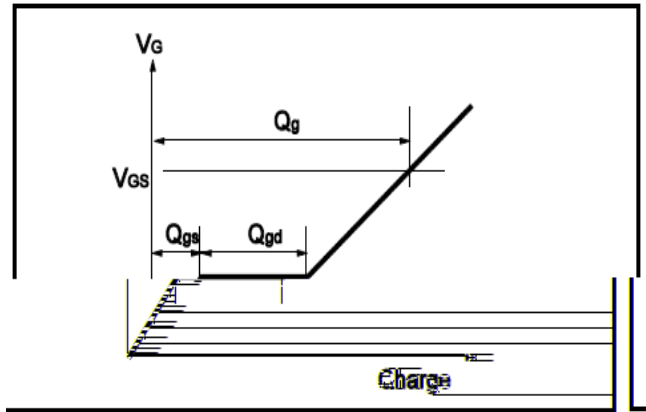


Fig.13 Resistive Switching Test Circuit

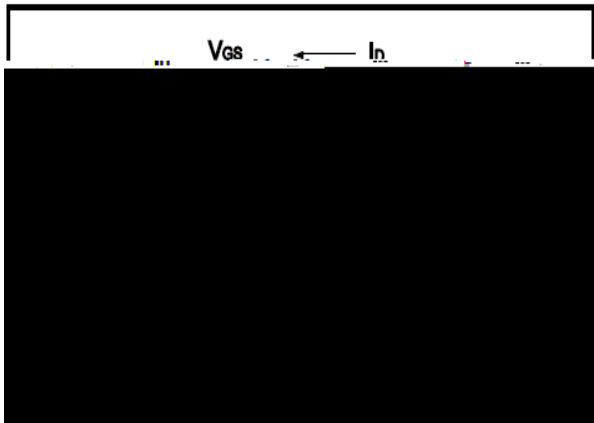


Fig.14 Resistive Switching Test Waveform

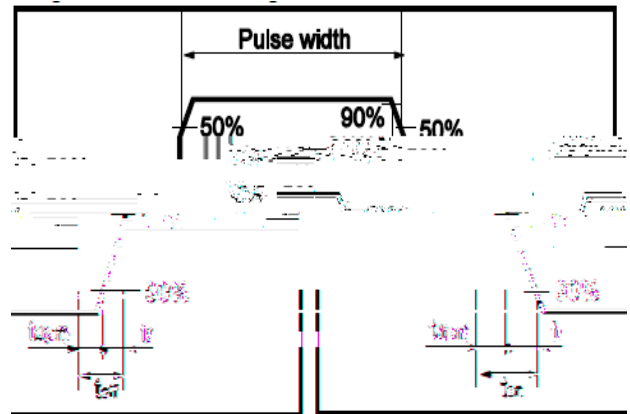


Fig.15 Avalanche Measurement Circuit

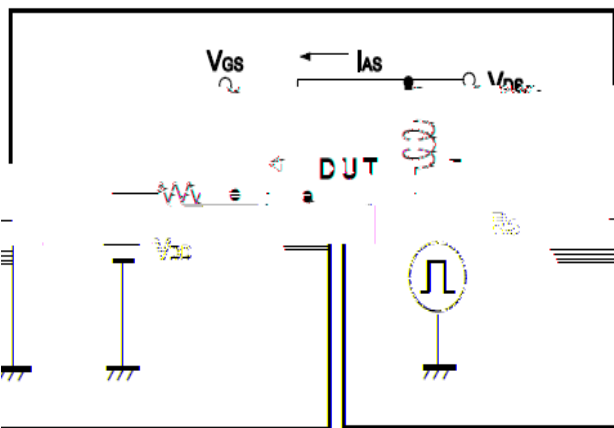
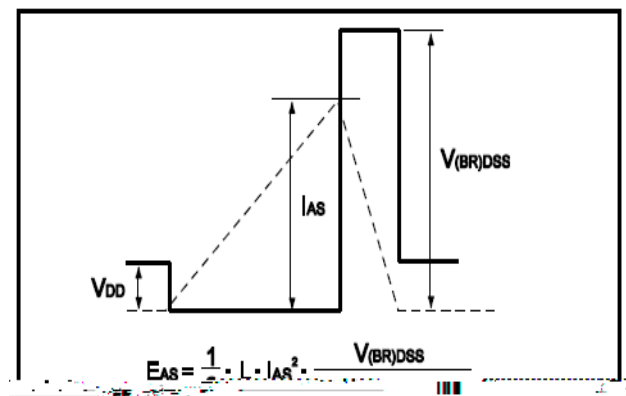


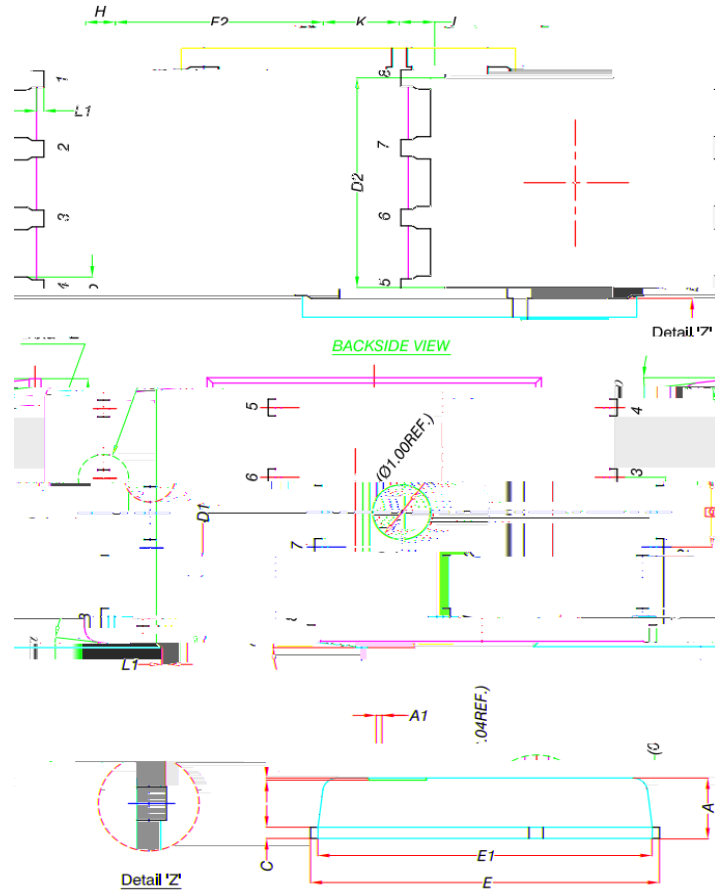
Fig.16 Avalanche Waveform





Dimensions DFN5x6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

1	5.70	5.75	5.80	E
E2	3.35	3.55	3.75	
e	1.27 BSC			
H	0.45	0.51	0.61	
K	1.10			
L1	0.31	0.51	0.61	
L2	0.20	0.06	0.1	

